Evelina Domashevskaya

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5436796/publications.pdf

Version: 2024-02-01

186 papers 1,670 citations

331670 21 h-index 31 g-index

188 all docs

188 docs citations

times ranked

188

1375 citing authors

#	Article	lF	Citations
1	Electronic structure of the full-Heusler Co\$\$_{2-x}\$\$Fe\$\$_{1+x}\$\$Si and half-Heusler CoFeSi alloys obtained by first-principles calculations and ultrasoft X-ray emission spectroscopy. European Physical Journal B, 2022, 95, 1.	1.5	3
2	Bound oxygen influence on the phase composition and electrical properties of semi-insulating silicon films. Materials Science in Semiconductor Processing, 2021, 121, 105287.	4.0	O
3	The state of individual layers and interfaces in multilayer nanostructures [(<i>C>o</i> ₄₀ <i>F</i> ₄₀ 40 <i>B</i> ₂₀) ₃₄ (<i>Surface and Interface Analysis, 2021, 53, 244-249.</i>	5 <b 1:8i>i </td <td>/i>₫i>O<st< td=""></st<></td>	/i>₫i>O <st< td=""></st<>
4	Features of the two-stage formation of macroporous and mesoporous silicon structures \tilde{N}_{\bullet} Kondensirovannye Sredy Mezhfaznye Granitsy, 2021, 23, 41-48.	0.3	0
5	Effect of Phase Transformations of a Metal Component on the Magneto-Optical Properties of Thin-Films Nanocomposites (CoFeZr)x (MgF2)100â ⁻² x. Nanomaterials, 2021, 11, 1666.	4.1	3
6	Investigation of the Magnetic Properties of Amorphous Multilayer Nanostructures [(CoFeB)60C40/SiO2]200 and [(CoFeB)34(SiO2)66/C]46 by the Transversal Kerr Effect. Kondensirovannye Sredy Mezhfaznye Granitsy, 2020, 22, 438-445.	0.3	0
7	ВлиÑĐ½Đ¸Đµ ÑĐ»Đ°Đ±Đ¾Đ³Đ¾ Đ¸Đ¼Đ¿ÑƒĐ»ÑŒÑĐ½Đ¾Đ3Đ¾ ÑлеаÑ,Ñ€Đ¾Đ¼Đ°Đ₃Đ½Đ¸Ñ,Đ½	Đ ¾.₿ ³Đ¾	4 Đ⊋Đ¾Đ»Ñ∙E
8	On the Morphology and Optical Properties of Molybdenum Disulfide Nanostructures from a Monomolecular Layer to a Fractal-Like Substructure. Semiconductors, 2019, 53, 923-929.	0.5	2
9	Oscillating fine structure of x-ray absorption and atomic structure of metallic layers in a magnetic multilayer nanostructure (Đ¡o45Fe45Zr10/SiO2)n. Materials Research Express, 2019, 6, 1150g9.	1.6	2
10	A study of multilayer nanostructures [(Co ₄₅ Fe ₄₅ Zr ₁₀) ₃₅ (Al ₂ O ₃) <sub [(co₄₅ Fe ₄₅ Zr ₁₀) ₃₅ (Al ₂ O ₃) <sub>)<sub< td=""><td>0.7</td><td>3</td></sub<></sub>	0.7	3
11	by means of XRD, XRR, IR spectroscopy, and USXES. EPJ Applied Physics, 2019, 87, 21301. Influence of the Crystal Structure of the Nucleus on the Morphology of t-ZnO Tetrapods. Crystallography Reports, 2019, 64, 212-215.	0.6	2
12	Effect of Process Conditions on the Structure and Optical Properties of MoO3 Produced by Vapor Transport Deposition. Inorganic Materials, 2019, 55, 49-58.	0.8	2
13	The Influence of Relative Content of a Metal Component in a Dielectric Matrix on the Formation and Dimensions of Cobalt Nanocrystallites in Cox(MgF2)100–Âx Film Composites. Physics of the Solid State, 2019, 61, 71-79.	0.6	9
14	ĐœĐ•Đ–ĐĐ¢ĐžĐœĐЫЕ Đ¡Đ'Đ⁻Đ—Đ⁻ Đ' ĐĐœĐžĐĐĐĐ«Đ¥ ĐšĐžĐœĐŸĐžĐ—Đ⁻Đ¢ĐĐ¥ (CoFeB)x(TiO2)1–x	C ĐOĐĐ —Đ	Ð∢МСОÐ
15	ВлиÑĐ½Đ¸Đµ Ñ€ĐµĐ¶Đ¸Đ¼Đ¾Đ² ÑлеаÑ,Ñ€Đ¾Ñ…Đ¸Đ¼Đ¸Ñ‡ĐµÑĐ°Đ¾Đ¾ Ñ,Ñ€Đ°Đ²Đ»ĐµĐ½Đ¸Ñ	ĺ•ĐQÑ¥€Đ¸€	D3 /4D
16	Đ¢Đ¾Đ¿Đ¾Đ»Đ¾Đ³Đ¸Ñ‡ĐμÑĐ°Đ°Ñ•Đ¼Đ¾ĐѢμĐ»ÑŒ ÑÑ,Ñ€ÑƒĐ°Ñ,уры и Đ½ĐμĐ»Đ¸Đ½ĐμĐ¹Đ½Đ°Ñ	•Đ ¼\$ ³¼Đ	ŒÑ"ł
17	Photoluminescence Properties of Nanoporous Nanocrystalline Carbonate-Substituted Hydroxyapatite. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018, 124, 187-192.	0.6	5
18	Study of the nanoporous CHAP photoluminiscence for developing the precise methods of early caries detection. IOP Conference Series: Materials Science and Engineering, 2018, 307, 012027.	0.6	1

#	Article	IF	Citations
19	IR Spectroscopic Study of Interatomic Interaction in [(CoFeB)60C40/SiO2]200 and [(CoFeB)34(SiO2)66/C]46 Multilayer Nanostructures with Metal-Containing Composite Layers. Inorganic Materials, 2018, 54, 140-146.	0.8	3
20	Phase Formation and Electronic Structure Peculiarities in the Al1 $\hat{a} \in "xSi \times Film$ Composites under the Conditions of Magnetron and Ion-Beam Sputtering. Physics of the Solid State, 2018, 60, 1021-1028.	0.6	1
21	Phase composition of the buried silicon interlayers in the amorphous multilayer nanostructures [(<scp>Co< scp>_{45< sub><scp>Fe< scp>_{45< sub><scp>Zr< scp>_{10< sub>) <i>a< i>a</i>}</scp><and [(<scp="">Co< scp>_{45< sub><scp>Fe< scp>_{45< sub><scp>Zr< scp>_{10< sub>)_{35< sub>(<}}</scp>}</scp>}</and>}</scp>}</scp>	1.8	12
22	Surface and Interface Analysis, 2018, 50, 1265-1270. Composition of nanocomposites of thin tin layers on porous silicon, formed by magnetron sputtering. Physics of the Solid State, 2017, 59, 791-800.	0.6	0
23	Formation of silicon nanocrystals in multilayer nanoperiodic a-SiO x /insulator structures from the results of synchrotron investigations. Semiconductors, 2017, 51, 349-352.	0.5	5
24	Electronic structure and phase composition of silicon oxide in the metal-containing composite layers of a [(Co40Fe40B20)34(SiO2)66/C]46 multilayer amorphous nanostructure with carbon interlayers. Inorganic Materials, 2017, 53, 930-936.	0.8	3
25	X-ray and x-ray electron spectroscopy of new materials. Journal of Structural Chemistry, 2017, 58, 1057-1060.	1.0	4
26	Excitation of luminescence of the nanoporous bioactive nanocrystalline carbonate-substituted hydroxyapatite for early tooth disease detection. Results in Physics, 2017, 7, 3853-3858.	4.1	7
27	Electronic structure and phase composition of dielectric interlayers in multilayer amorphous nanostructure [(CoFeB)60C40/SiO2]200. Physics of the Solid State, 2017, 59, 168-173.	0.6	5
28	Specific features of the atomic structure of metallic layers of multilayered (CoFeZr/SiO2)32 and (CoFeZr/a-Si)40 nanostructures with different interlayers. Physics of the Solid State, 2017, 59, 385-391.	0.6	1
29	Composition of nanocomposites based on thin layers of tin on porous silicon formed by magnetron sputtering. Physica B: Condensed Matter, 2017, 504, 1-8.	2.7	2
30	Systems of silicon nanocrystals and their peculiarities. Series in Materials Science and Engineering, 2017, , 107-154.	0.1	0
31	Ab initio calculation and synchrotron X-ray spectroscopy investigations of tin oxides near the Sn L 3 absorption edges. Physics of the Solid State, 2016, 58, 2379-2384.	0.6	1
32	A soft X-ray synchrotron study of the charge state of iron ions in the ferrihydrite core of the ferritin Dps protein in Escherichia coli. Biophysics (Russian Federation), 2016, 61, 705-710.	0.7	11
33	Small-angle diffraction by heterogeneous composite nanostructures based on (Co45Fe45Zr10)35(Al2O3)65. Bulletin of the Russian Academy of Sciences: Physics, 2016, 80, 1407-1410.	0.6	1
34	The electronic structure peculiarities of a strained silicon layer in silicon-on-insulator: Experimental and theoretical data. Applied Surface Science, 2016, 382, 331-335.	6.1	1
35	A novel approach to the electronic structure and surface composition investigations of tin-oxygen system materials by means of X-ray absorption spectroscopy combined with ab initio calculations. Computational Materials Science, 2016, 121, 119-123.	3.0	17
36	Interatomic interactions at interfaces of multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2016, 58, 1024-1033.	0.6	6

#	Article	IF	CITATIONS
37	Composition and optical properties of amorphous a-SiO x :H films with silicon nanoclusters. Semiconductors, 2016, 50, 212-216.	0.5	3
38	Deep Centers at the Interface in In2x Ga2(1–x)Te3/InAs and In2Te3/InAs Heterostructures. Semiconductors, 2016, 50, 309-313.	0.5	0
39	On the electrical and optical properties of oxide nanolayers produced by the thermal oxidation of metal tin. Semiconductors, 2016, 50, 180-184.	0.5	O
40	Atomic and electronic structure of amorphous and nanocrystalline layers of semi-insulating silicon produced by chemical-vapor deposition at low pressures. Journal of Surface Investigation, 2015, 9, 1228-1236.	0.5	4
41	Synchrotron characterization of functional tin dioxide nanowires. AIP Conference Proceedings, 2015,	0.4	O
42	Peculiarities of electronic structure of silicon-on-insulator structures and their interaction with synchrotron radiation. Modern Electronic Materials, 2015 , 1 , $67-72$.	0.6	0
43	Peculiarities of the electronic structure and phase composition of amorphous (SiO2) x (a-Si: H) x–1 composite films according to X-ray spectroscopy data. Technical Physics Letters, 2015, 41, 1010-1012.	0.7	5
44	Women physicists in Russia in a period of new reforms in fundamental science and higher education. AIP Conference Proceedings, 2015, , .	0.4	0
45	Atomic and electronic structure peculiarities of silicon wires formed on substrates with varied resistivity according to ultrasoft X-ray emission spectroscopy. Technical Physics Letters, 2015, 41, 344-347.	0.7	5
46	Investigations of the composition of macro-, micro- and nanoporous silicon surface by ultrasoft X-ray spectroscopy and X-ray photoelectron spectroscopy. Applied Surface Science, 2015, 359, 550-559.	6.1	15
47	XANES and XPS investigations of surface defects in wire-like SnO2 crystals. Physics of the Solid State, 2015, 57, 153-161.	0.6	36
48	Formation of Si nanocrystals in multilayered nanoperiodic Al2O3/SiO \times /Al2O3/SiO \times //Si(100) structures: Synchrotron and photoluminescence data. Semiconductors, 2015, 49, 409-413.	0.5	4
49	Variations of the optical characteristics of nano-, meso-, and macroporous silicon with time. Technical Physics, 2015, 60, 1096-1100.	0.7	2
50	Structure and composition of metal-substituted calcium-deficient hydroxyapatite. Journal of Surface Investigation, 2014, 8, 1128-1136.	0.5	12
51	X-Ray photoelectron spectroscopy investigations of atomic interactions in surface layers of multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2014, 56, 2294-2306.	0.6	9
52	Specific features of the electronic and atomic structures of silicon single crystals in the aluminum matrix. Physics of the Solid State, 2014, 56, 2543-2547.	0.6	1
53	Synthesis of europium-doped zinc oxide micro- and nanowires. Russian Journal of Physical Chemistry A, 2014, 88, 108-111.	0.6	5
54	Optical characteristics of porous silicon structures. Technical Physics, 2014, 59, 224-229.	0.7	27

#	Article	IF	Citations
55	Synchrotron studies of SnO2 wire-like crystals. Journal of Surface Investigation, 2014, 8, 111-116.	0.5	6
56	Theoretical and experimental study of the electronic structure of tin dioxide. Physics of the Solid State, 2014, 56, 1748-1753.	0.6	16
57	Specific features of the sol-gel formation and optical properties of 3d metal/porous silicon composites. Semiconductors, 2014, 48, 551-555.	0.5	5
58	XANES investigations of interatomic interactions in multilayered nanostructures (Co45Fe45Zr10/a-Si)40 and (Co45Fe45Zr10/SiO2)32. Physics of the Solid State, 2013, 55, 1294-1303.	0.6	9
59	Synchrotron investigations of Si/Mo/Si…c-Si (100) multilayer nanoperiodic structures. Physics of the Solid State, 2013, 55, 634-641.	0.6	4
60	Properties of epitaxial (Al x Ga1 \hat{a} ' x As)1 \hat{a} ' y C y alloys grown by MOCVD autoepitaxy. Semiconductors, 2013, 47, 7-12.	0.5	7
61	Structural and optical properties of porous silicon prepared from a p +-epitaxial layer on n-Si(111). Technical Physics, 2013, 58, 404-407.	0.7	1
62	Structural features and surface morphology of AlxGayIn1â^'xâ^'yAszP1â^'z/GaAs(100) heterostructures. Applied Surface Science, 2013, 267, 181-184.	6.1	23
63	The problem of XANES spectrum interpretation measured by TEY technique at different photon glancing angles. Journal of Electron Spectroscopy and Related Phenomena, 2013, 191, 35-40.	1.7	1
64	Synchrotron study of the formation of nanoclusters in Al2O3/SiO x /Al2O3/SiO x /…/Si(100) multilayer nanostructures. Semiconductors, 2013, 47, 1316-1323.	0.5	6
65	Photoluminescence properties of heavily doped heterostructures based on (Al x Ga1 \hat{a} ° x As)1 \hat{a} ° y Si y solid solutions. Physics of the Solid State, 2013, 55, 2169-2172.	0.6	10
66	The synthesis and optical properties of different zinc oxide nanostructures. Russian Journal of Physical Chemistry A, 2013, 87, 2246-2252.	0.6	3
67	Synthesis of nanocrystalline hydroxyapatite by precipitation using hen's eggshell. Ceramics International, 2013, 39, 4539-4549.	4.8	108
68	Electronic structure of undoped and doped SnOx nanolayers. Thin Solid Films, 2013, 537, 137-144.	1.8	16
69	Optical properties of porous silicon processed in tetraethyl orthosilicate. Technical Physics, 2013, 58, 284-288.	0.7	14
70	Investigations of Porous Silicon with Deposited 3D-Metals by Auger- and Ultrasoft X-Ray Emission Spectroscopy. Journal of Nanoscience and Nanotechnology, 2012, 12, 8806-8810.	0.9	2
71	Interference phenomena of synchrotron radiation in TEY spectra for silicon-on-insulator structure. Journal of Synchrotron Radiation, 2012, 19, 609-618.	2.4	5
72	Composition and reactivity of porous silicon nanopowders. Inorganic Materials, 2012, 48, 965-970.	0.8	6

#	Article	lF	Citations
73	Peculiarities of electron-energy structure of surface layers of porous silicon formed on p-type substrates. Inorganic Materials, 2012, 48, 1291-1297.	0.8	3
74	Study of the morphological growth features and optical characteristics of multilayer porous silicon samples grown on n-type substrates with an epitaxially deposited p +-layer. Semiconductors, 2012, 46, 1079-1084.	0.5	23
75	Synchrotron investigation of the multilayer nanoperiodical Al ₂ O ₃ /SiO/Al ₂ O ₃ /SiO…Si structure formation. Surface and Interface Analysis, 2012, 44, 1182-1186.	1.8	4
76	AES and XPS investigations of the surface layers of porous silicon with Fe, Co, and Ni embedded pores. Journal of Surface Investigation, 2012, 6, 106-110.	0.5	9
77	Structural and spectral features of MOCVD Al x Ga y In1 â^' x â^' y As z P1 â^' z /GaAs (100) alloys. Semiconductors, 2012, 46, 719-729.	0.5	18
78	Influence of natural aging on photoluminescence from porous silicon. Technical Physics, 2012, 57, 305-307.	0.7	15
79	XPS study of the oxidation of nanosize Ni/Si(100) films. Journal of Structural Chemistry, 2011, 52, 115-122.	1.0	8
80	Effect of natural aging on photoluminescence of porous silicon. Technical Physics Letters, 2011, 37, 789-792.	0.7	20
81	Synchrotron radiation interference in front of the silicon absorption edge for silicon-on-insulator structures. Journal of Surface Investigation, 2011, 5, 141-149.	0.5	4
82	Synchrotron investigations of electronic and atomic-structure peculiarities for silicon-oxide films' surface layers containing silicon nanocrystals. Journal of Surface Investigation, 2011, 5, 958-967.	0.5	7
83	X-ray diffraction and IR spectroscopy investigation of synthesized and biogenic nanocrystalline hydroxyapatite. Journal of Surface Investigation, 2011, 5, 1162-1167.	0.5	19
84	Effect of silicon on relaxation of the crystal lattice in MOCVD–hydride Al x Ga1 â~' x As:Si/GaAs(100) heterostructures. Semiconductors, 2011, 45, 481-492.	0.5	23
85	Spinodal Decomposition of Ga x In1â^'x As y P1â^'y Quaternary Alloys. Semiconductors, 2011, 45, 1433-1440.	0.5	23
86	Spectral features of Co–Ge–Te amorphous thin film. Optics and Laser Technology, 2011, 43, 20-24.	4.6	15
87	Features of atomic and electronic structure of oxides on porous silicon surface according to XANES data. Journal of Surface Investigation, 2010, 4, 384-389.	0.5	2
88	The substructure and luminescence of low-temperature AlGaAs/GaAs(100) heterostructures. Semiconductors, 2010, 44, 184-188.	0.5	23
89	Relaxation of crystal lattice parameters and structural ordering in $\ln x \text{Ga1 \^{a}}$ x As epitaxial alloys. Semiconductors, 2010, 44, 1106-1112.	0.5	7
90	Morphology of tin oxide nanocrystals grown by vapor-phase transport method. Technical Physics Letters, 2010, 36, 541-543.	0.7	0

#	Article	IF	CITATIONS
91	Atomic and electronic structure of the surface of porous silicon layers. Russian Journal of General Chemistry, 2010, 80, 1128-1135.	0.8	1
92	Effect of the temperatures on structural and optical properties of tin oxide (SnOx) powder. Physica B: Condensed Matter, 2010, 405, 313-317.	2.7	15
93	Raman investigation of low temperature AlGaAs/GaAs(100) heterostructures. Physica B: Condensed Matter, 2010, 405, 2694-2696.	2.7	26
94	Structural and optical investigations of AlxGa1â^'xAs:Si/GaAs(100) MOCVD heterostructures. Physica B: Condensed Matter, 2010, 405, 4607-4614.	2.7	25
95	Structural, microstructural and optical properties of multiphase Ge–Co–Te system. Physica B: Condensed Matter, 2010, 405, 2107-2109.	2.7	1
96	Compensation temperatures induced by longitudinal fields in a mixed spin Ising ferrimagnet. Solid State Communications, 2010, 150, 1253-1257.	1.9	12
97	XANES, USXES and XPS investigations of electron energy and atomic structure peculiarities of the silicon suboxide thin film surface layers containing Si nanocrystals. Surface and Interface Analysis, 2010, 42, 891-896.	1.8	14
98	XRD and Raman Study of Low Temperature AlGaAs/GaAs (100) Heterostructures. NATO Science for Peace and Security Series B: Physics and Biophysics, 2010, , 225-236.	0.3	3
99	10.1007/s11451-008-1025-0. , 2010, 50, 139.		0
100	Synthesis and Microscopic Characterization of In ₂ O ₃ SUB>Hetero-Junction Beaded Nanowires. Journal of Advanced Microscopy Research, 2010, 5, 63-66.	0.3	0
101	Evolution of nanoporous silicon phase composition and electron energy structure under natural ageing. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1651-1655.	0.8	23
102	Role of the buffer porous layer and dysprosium doping in GalnPâ€porGaAsâ€GaAs heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1694-1696.	0.8	1
103	Electron structure of iron and cobalt nanocomposites on the basis of porous silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1656-1660.	0.8	3
104	Electron structure of porous silicon obtained without the use of HF acid. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1557-1560.	0.8	13
105	Spin compensation temperatures in the mean-field approximation of a mixed spin-2 and spin-5/2 Ising ferrimagnetic system. Physica A: Statistical Mechanics and Its Applications, 2009, 388, 4713-4718.	2.6	18
106	Preparation of porous silicon nanocomposites with iron and cobalt and investigation of their electron structure by X-ray spectroscopy techniques. Technical Physics Letters, 2009, 35, 827-830.	0.7	11
107	The formation of tin oxides in thin-film Sn/C/KCl(100) structures. Crystallography Reports, 2009, 54, 110-115.	0.6	4
108	The effects of the porous buffer layer and doping with dysprosium on internal stresses in the GalnP:Dy/por-GaAs/GaAs(100) heterostructures. Semiconductors, 2009, 43, 1098-1101.	0.5	0

#	Article	IF	CITATIONS
109	Phase formation under the effect of spinodal decomposition in epitaxial alloys of Ga \times In1 \hat{a} \hat{a} \times P/GaAs(100) heterostructures. Semiconductors, 2009, 43, 1221-1225.	0.5	5
110	Structural and optical properties of low-temperature hydride-MOCVD AlGaAs/GaAs(100) heterostructures based on omission solid solutions. Semiconductors, 2009, 43, 1610-1616.	0.5	9
111	Temperature dependence of liquid volume. Technical Physics, 2009, 54, 1082-1084.	0.7	4
112	Structure and photoluminescence properties of SnO ₂ nanowires synthesized from SnO powder. EPJ Applied Physics, 2009, 48, 10603.	0.7	10
113	Electronic and energy structure and X-ray spectra of Zn3P2 and Cd3P2 and their solid solution (Cd0.5Zn0.5)3P2. Journal of Structural Chemistry, 2008, 49, 59-62.	1.0	3
114	XPS and XANES studies of SnO x nanolayers. Journal of Structural Chemistry, 2008, 49, 80-91.	1.0	23
115	Investigations of porous InP properties by XRD, IR, USXES, XANES and PL techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 144-147.	3.5	7
116	Structure, elemental composition, and mechanical properties of films prepared by radio-frequency magnetron sputtering of hydroxyapatite. Glass Physics and Chemistry, 2008, 34, 608-616.	0.7	8
117	Kinetics of resistive response of SnO2 \hat{a} ° x thin films in gas environment. Semiconductors, 2008, 42, 481-485.	0.5	4
118	Infrared reflection spectra of multilayer epitaxial heterostructures with embedded InAs and GaAs layers. Semiconductors, 2008, 42, 1055.	0.5	6
119	Composition and parameters of domains resulting from spinodal decomposition of quaternary alloys in epitaxial GalnP/Ga x In1 â^² x As y P1 â^² y /GalnP/GaAs(001) heterostructures. Semiconductors, 2008, 42, 1069-1075.	0.5	9
120	XANES and USXES studies of interatomic interactions in (Co41Fe39B20) x (SiO2)1 \hat{a} x nanocomposites. Physics of the Solid State, 2008, 50, 139-145.	0.6	7
121	Investigation of porous InP by X-ray diffraction, IR spectroscopy, USXES, XANES spectroscopy, and photoluminescence. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 439-442.	0.6	4
122	XANES study of interatomic interactions in (CoFeZr) x (SiO2)1â€"x nanocomposites. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 448-452.	0.6	5
123	X-ray photoelectron spectroscopy of tin oxide nanolayers. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 504-509.	0.6	3
124	Synchrotron study of laser-thermally oxidized thin titanium films. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 510-514.	0.6	0
125	ELECTRON STRUCTURE INVESTIGATIONS OF InGaP / GaAs (100) HETEROSTRUCTURES WITH InP QUANTUM DOTS. International Journal of Nanoscience, 2007, 06, 215-219.	0.7	O
126	XANES and USXES investigations of interatomic interaction at the grain boundaries in nanocomposites (Co41Fe39B20)x(SiO2)1â^'x. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 180-185.	1.7	9

#	Article	IF	Citations
127	Investigations of the electron energy structure and phase composition of porous silicon with different porosity. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 445-451.	1.7	15
128	Synchrotron investigations of the initial stage of tin nanolayers oxidation. Journal of Electron Spectroscopy and Related Phenomena, 2007, 156-158, 340-343.	1.7	12
129	Silicon nanocrystals in SiO2 matrix obtained by ion implantation under cyclic dose accumulation. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 16-20.	2.7	17
130	Synchrotron investigations of the electron structure of silicon nanocrystals in a SiO2 matrix. Journal of Surface Investigation, 2007, 1, 55-59.	0.5	3
131	SnOx obtaining by thermal oxidation of nanoscale tin films in the air and its characterization. Thin Solid Films, 2007, 515, 6350-6355.	1.8	23
132	XRD, AFM and IR investigations of ordered AlGaAs2 phase in epitaxial AlxGa1–xAs/GaAs (100) heterostructures. Surface and Interface Analysis, 2006, 38, 828-832.	1.8	24
133	TEM and XANES investigations and optical properties of SnO nanolayers. Surface and Interface Analysis, 2006, 38, 514-517.	1.8	17
134	Optical properties of SnO2â^'x nanolayers. Technical Physics Letters, 2006, 32, 782-784.	0.7	2
135	Infrared reflectance spectra and morphologic features of the surface of epitaxial AlxGa1â°x As/GaAs(100) heterostructures with the ordered AlGaAs2 phase. Semiconductors, 2006, 40, 406-413.	0.5	4
136	Vegard's law and superstructural phases in AlxGa1â^'x As/GaAs(100) epitaxial heterostructures. Semiconductors, 2005, 39, 336-342.	0.5	7
137	A study of the local electronic and atomic structure in a-SixC1â^'x amorphous alloys using ultrasoft X-ray emission spectroscopy. Semiconductors, 2005, 39, 830-834.	0.5	10
138	Synchrotron investigations of the specific features in the electron energy spectrum of silicon nanostructures. Physics of the Solid State, 2004, 46, 345-350.	0.6	9
139	Influence of ultrashort pulses of electromagnetic radiation on parameters of metal-insulator-semiconductor structures. Semiconductors, 2004, 38, 1390-1393.	0.5	O
140	Synchrotron investigations of an electron energy spectrum in III–V-based nanostructures. Semiconductors, 2003, 37, 992-997.	0.5	2
141	Influence of water vapor adsorption on the C-V characteristics of heterostructures containing porous silicon. Technical Physics, 2003, 48, 1442-1448.	0.7	7
142	Electronic structure of rhenium disilicides. Journal of Physics Condensed Matter, 2002, 14, 6833-6839.	1.8	11
143	USXES AND OPTICAL PHENOMENA IN SI LOW-DIMENSIONAL STRUCTURES DEPENDENT ON MORPHOLOGY AND SILICON OXIDE COMPOSITION ON SI SURFACE. Surface Review and Letters, 2002, 09, 1047-1052.	1.1	11
144	Defect formation and crystallization in a-Si:H induced by Si+ implantation. Journal of Non-Crystalline Solids, 2002, 299-302, 783-787.	3.1	0

#	Article	IF	Citations
145	A combined technique for studying the multicomponent spectra of photoreflection from semiconductors. Semiconductors, 2002, 36, 48-53.	0.5	2
146	Combined photoreflectance/photoluminescence studies of the stability of semiconductor surface passivation. Technical Physics, 2002, 47, 224-226.	0.7	0
147	Influence of laser pump density on the characteristic time constant and the intermediate-field electromodulation E 0 component of the photoreflectance signal. Semiconductors, 2002, 36, 153-156.	0.5	2
148	E 0 photoreflectance spectra of GaAs: Identification of the features related to impurity transitions. Semiconductors, 2002, 36, 259-262.	0.5	2
149	E 0 photoreflectance spectra of semiconductor structures with a high density of interface states. Semiconductors, 2002, 36, 784-788.	0.5	O
150	Title is missing!. Russian Physics Journal, 2002, 45, 405-413.	0.4	1
151	Determination of the phase composition of surface layers of porous silicon by ultrasoft X-ray spectroscopy and X-ray photoelectron spectroscopy techniques. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 895-900.	1.7	32
152	XPS and XES emission investigations of d–p resonance in some copper chalcogenides. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 901-908.	1.7	37
153	X-ray spectroscopic study of electronic structure of amorphous silicon and silicyne. Semiconductors, 2001, 35, 956-961.	0.5	6
154	Temperature dependence of residual stress in epitaxial GaAs/Si(100) films determined from photoreflectance spectroscopy data. Semiconductors, 2000, 34, 73-80.	0.5	8
155	Modifications of the structure and electrical parameters of the films of amorphous hydrogenated silicon implanted with Si+ ions. Semiconductors, 2000, 34, 87-91.	0.5	0
156	Generalized multilayer model for the quantitative analysis of the electromodulation components of the electroreflectance and photoreflectance spectra of semiconductors in the region of the E 0 fundamental transition. Semiconductors, 2000, 34, 1045-1051.	0.5	4
157	Combined photoreflectance/photoluminescence studies of the electronic properties of semiconductor surfaces. Physics of the Solid State, 2000, 42, 2200-2203.	0.6	0
158	Low-Energy Oscillations in the E[sub 0] Photoreflectance Spectra of Homoepitaxial n-GaAsâ^•n[sup +]-GaAs Samples with n = 10[sup 15]–10[sup 16] cm[sup –3] and n[sup +] ≈ 10[sup 18] cm[sup –3]. Cand Spectroscopy (English Translation of Optika I Spektroskopiya), 2000, 89, 549.	O pti cs	0
159	Application of semiconductor gas sensors for medical diagnostics. Sensors and Actuators B: Chemical, 1999, 59, 26-29.	7.8	120
160	Strain-induced photoreflectance spectra in the vicinity of the E 0 transition in GaAs/Si and InP/Si heterostructures. Physics of the Solid State, 1999, 41, 654-659.	0.6	0
161	Electron states in the surface region of gallium arsenide treated in selenium and arsenic vapor. Semiconductors, 1999, 33, 665-667.	0.5	0
162	Silicide formation in thin film Pt–Si(111) structure by USXES data. Thin Solid Films, 1997, 298, 135-137.	1.8	2

#	Article	IF	Citations
163	Variations of the local density of electron states and short-range order in amorphous hydrated silicon films. Physics of the Solid State, 1997, 39, 213-215.	0.6	0
164	AES and USXES investigations of the phase transformation in the surface layers of V-Si/SiO2/Si thin films structure stimulated by oxygen annealing. Journal of Electron Spectroscopy and Related Phenomena, 1995, 76, 511-516.	1.7	1
165	Theoretical Xâ€ray Emission Study of High― <i>T</i> _c Superconductor YBa ₂ Cu ₃ O ₇ Thin Films. Physica Status Solidi (B): Basic Research, 1994, 185, 179-187.	1.5	4
166	Temperature influence on the energy characteristics of HTS YBa2Cu3O7 (Ag) and magnetron sputtered films studied by XPS and XES. Journal of Electron Spectroscopy and Related Phenomena, 1994, 68, 445-451.	1.7	0
167	Local non-stoichiometry in superconducting and ferroelectric films of complex oxides. Ferroelectrics, 1992, 130, 175-185.	0.6	1
168	Electronic structure of a-Si3N4: AB initio cluster calculations and soft X-ray emission spectroscopy study. Journal of Non-Crystalline Solids, 1989, 114, 495-497.	3.1	6
169	Theoretical and X-ray spectral investigations of density of states in amorphous silicon-germanium layers. Journal of Non-Crystalline Solids, 1987, 90, 127-130.	3.1	0
170	Density of states and photoconductivity in hydrogenated amorphous silicon. Journal of Non-Crystalline Solids, 1987, 90, 135-138.	3.1	8
171	Changing of density of states in amorphous silicon nitride at degradation of its electric propertoes using soft X-ray spectroscopy. Journal of Non-Crystalline Solids, 1987, 97-98, 827-830.	3.1	2
172	Density of States and Photoconductivity of Hydrogenated Amorphous Silicon. Physica Status Solidi (B): Basic Research, 1986, 138, 647-653.	1.5	4
173	Integration over the Twoâ€Dimensional Brillouin Zone. Physica Status Solidi (B): Basic Research, 1985, 129, 293-299.	1.5	16
174	Localâ€Densityâ€Functional Approximation to the Energy Band Structure of TmS Using the Selfâ€Consistent Relativistic Linearizedâ€Augmentedâ€Plancâ€Wave Method. Physica Status Solidi (B): Basic Research, 1984, 121, 241-253.	1.5	9
175	d—s, p Resonance and Electronic Structure of Compounds, Alloys, and Solid Solutions. Physica Status Solidi (B): Basic Research, 1981, 105, 121-127.	1.5	36
176	Role of Noble Metal dâ€States in the Formation of the Electron Structure of Ternary Sulphides. Physica Status Solidi (B): Basic Research, 1981, 106, 429-435.	1.5	20
177	APW-LCAO energy bands and fundamental absorption in silver chloride crystal. Solid State Communications, 1981, 40, 559-562.	1.9	12
178	Problems of the OPW Method. II. Calculation of the Band Structure of ZnS and CdS. Physica Status Solidi (B): Basic Research, 1980, 97, 631-640.	1.5	18
179	Valence-level structure of phosphides of 3d-metals on the basis of XRS and ESCA data. Journal of Electron Spectroscopy and Related Phenomena, 1979, 16, 441-453.	1.7	25
180	X-ray spectral and X-ray electron study of complex oxides of Rh. Journal of Structural Chemistry, 1979, 20, 37-41.	1.0	1

#	Article	IF	CITATIONS
181	Problems of the OPW method. I. Transition metals. Physica Status Solidi (B): Basic Research, 1979, 94, 51-62.	1.5	8
182	The electron structure and interatomic interactions in the bpxas1â°x system. Journal of the Less Common Metals, 1979, 67, 229-235.	0.8	2
183	On a study of the valence band structure of boron and some of its compounds by the X-ray spectral method. Journal of the Less Common Metals, 1976, 47, 189-193.	0.8	23
184	Participation of d-electrons of metals of groups I, II, and III in chemical bonding with sulphur. Journal of Electron Spectroscopy and Related Phenomena, 1976, 9, 261-267.	1.7	24
185	A study by XPS and XRS of the participation in chemical bonding of the 3d electrons of copper, zinc and gallium. Journal of Electron Spectroscopy and Related Phenomena, 1975, 6, 231-238.	1.7	60
186	Band structure and density of states in SiP ₂ . Physica Status Solidi (B): Basic Research, 1975, 72, 661-665.	1.5	7